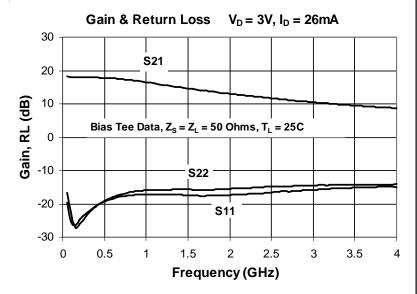


Sirenza Microdevices<sup>7</sup> SGC-2363Z is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with a patented active-bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 3V supply, the SGC-2363Z does not require a dropping resistor as compared to typical Darlington amplifiers. The SGC-2363Z is designed for high linearity 3V gain block applications that require small size and minimal external components. It is internally matched to 50 ohms.



# SGC-2363Z

# 50-4000 MHz Active Bias Silicon Germanium Cascadable Gain Block





# **Product Features**

- Single, Fixed 3V Supply
- No Dropping Resistor Required
- Patented Self-Bias Circuitry
- P1dB = 10.1 dBm at 1950 MHz
- OIP3 = 23 dBm at 1950 MHz
- Robust 1000V ESD, Class 1C HBM

## Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS, WCDMA
- IF Amplifier
- Wireless Data, Satellite

Symbol	Parameters	Units	Frequency	Min.	Тур.	Max.	
			850 MHz	15.5	17.0	18.5	
G	Small Signal Gain	dB	1950 MHz	11.6	13.1	14.6	
			2400 MHz		12.3		
			850 MHz		10.4		
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm	1950 MHz	9.1	10.1		
			2400 MHz		9.6		
		dBm	850 MHz		23.0		
OIP <sub>3</sub>	Output Third Order Intercept Point		1950 MHz	21	23.0		
			2400 MHz		24.0		
IRL	Input Return Loss	dB	1950 MHz	12.0	15.0		
ORL	Output Return Loss	dB	1950 MHz	10.5	14.5		
NF	Noise Figure	dB	1930 MHz		3.7	4.8	
V <sub>D</sub>	Device Operating Voltage	V			3		
Ι <sub>D</sub>	Device Operating Current	mA		22	26	30	
Rth, j-l	Thermal Resistance (junction to lead)	°C/W			255		
Test Conditio	<b>Test Conditions:</b> $V_D = 3.0V$ $I_D = 26mA$ $T_L = 25^{\circ}$		IP <sub>3</sub> Tone Spacing =	= 1MHz			
	Bias Tee Data $Z_S = Z_L = 50$ Ohms	Po	out per tone = -5 dBm				

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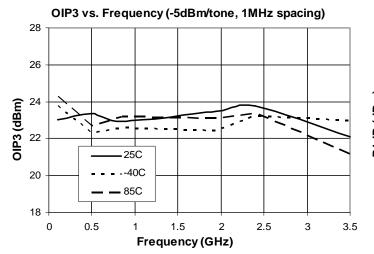
303 S. Technology Ct. Broomfield, CO 80021

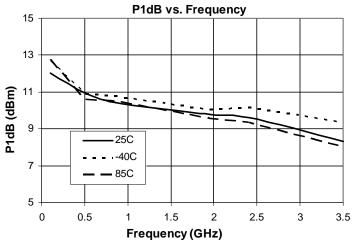
EDS-104973 Rev C



Symbol	Parameter	Unit	Frequency (MHz)					
Gymbol	i arameter		100	500	850	1950	2400	3500
G	Small Signal Gain	dB	18.4	18.1	17.0	13.1	12.3	9.8
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm	23.0	23.5	23.0	23.0	24.0	22.0
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm	12.1	11.0	10.4	10.1	9.6	8.3
IRL	Input Return Loss	dB	23.5	19.0	18.0	15.0	16.5	14.0
ORL	Output Return Loss	dB	22.5	18.5	16.5	14.5	13.0	12.5
S <sub>12</sub>	Reverse Isolation	dB	20.5	21.5	22.0	20.5	20.0	19.0
NF	Noise Figure	dB	2.9	3.0	3.3	3.7	3.9	4.7

## Typical Performance with Bias Tee, $V_{D}$ = 3V, $I_{D}$ = 26mA





Absolute Maximu	m Ratings	Reliability & Qualification Information				
Parameter	Absolute Limit	Parameter	Rating			
Max Device Current (I <sub>CE</sub> )	55 mA	ESD Rating - Human Body Model (HBM)				
Max Device Voltage (V <sub>CE</sub> )	4.5 V	Moisture Sensitivity Level	MSL 1			
Max. RF Input Power* (See Note)	+18 dBm	This product qualification report can be downloaded at				
Max. Junction Temp. (T <sub>J</sub> )	+150°C	www.sirenza.com				
Operating Temp. Range (T <sub>L</sub> )	-40°C to +85°C					
Max. Storage Temp. +150°C		Caution: ESD sensitive				
* <b>Note:</b> Load condition, $Z_L = 50$ Ohms		Appropriate precautions in handling, particular and testing devices must be observed	Appropriate precautions in handling, packaging and testing devices must be observed			
Operation of this device howend any one	of those limits may cause	<b>9</b>				

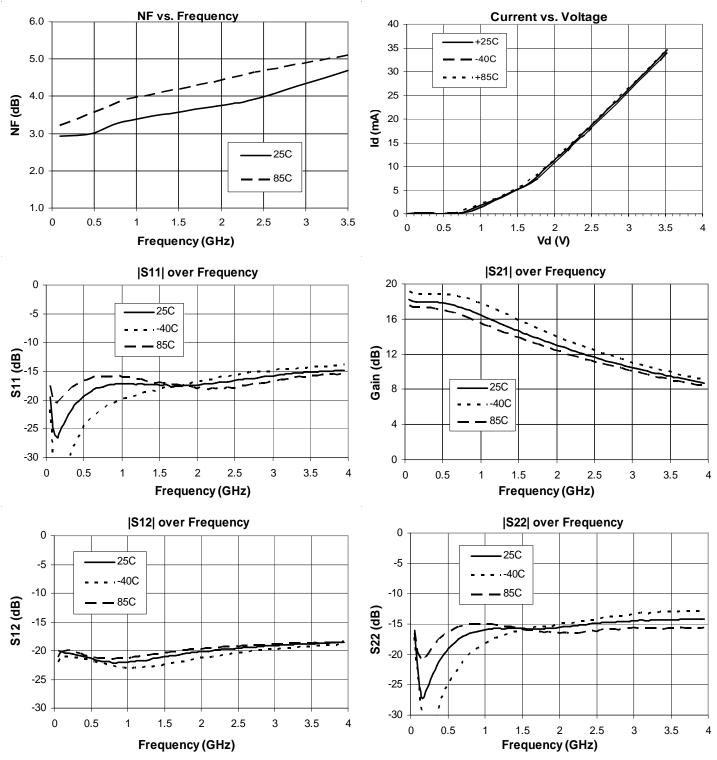
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:  $I_D V_D < (T_J - T_L) / R_{TH}, j-I \qquad T_L = T_{LEAD}$ 

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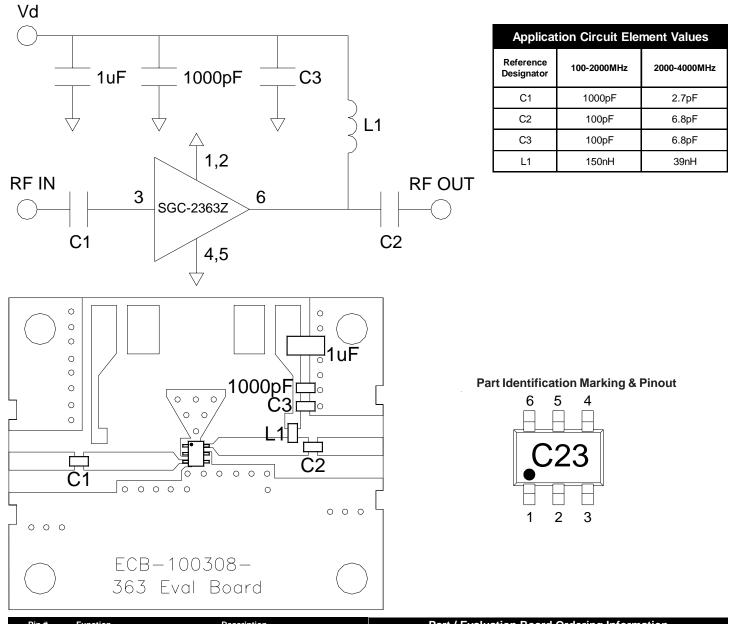






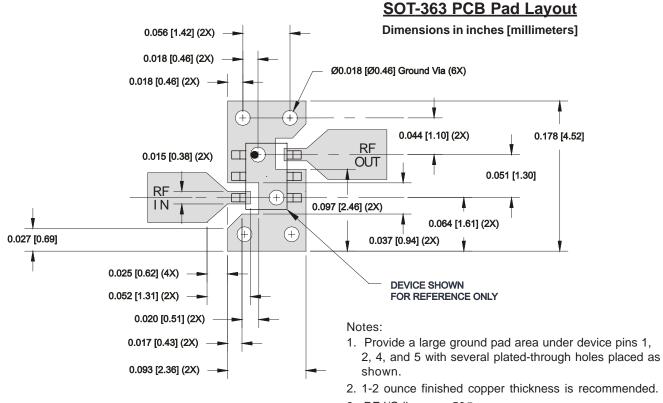
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Pin #	Function	Description	Part / Evaluation Board Ordering Information				
3		RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation	Part Number Description		Reel Size	Devices / Reel	
	GND	Connection to ground. Use via holes as close to the device ground leads as possible to reduce ground inductance and achieve optimum RF performance	SGC-2363Z	Lead Free, RoHs Compliant	7"	3000	
1,2,4,5			SGC-2363Z-EVB1	100-2000 MHz Evaluation Board	N/A	N/A	
	RF OUT /	RF output and bias pin. This pin requires the use of an	SGC-2363Z-EVB2	2000-4000 MHz Evaluation Board	N/A	N/A	
6	C BIAS external DC blocking capacitor chosen for the frequency of operation.						

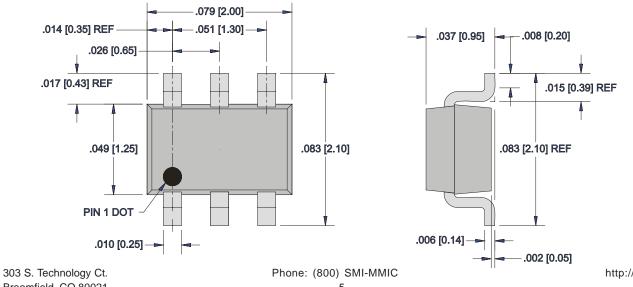




3. RF I/O lines are  $50\Omega$ 

#### SOT-363 Nominal Package Dimensions

**Dimensions in inches [millimeters]** A link to the SOT-363 package outline drawing with full dimensions and tolerances may be found on the product web page at www.sirenza.com.



Broomfield, CO 80021